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Kind regards,

Team Nexperia



PBSS3540E 40 V, 500 mA PNP low V_{CEsat} (BISS) transistor Rev. 02 — 11 December 2009

Product data sheet

Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough in Small Signal (BISS) transistor in a SOT416 (SC-75) SMD plastic package.

NPN complement: PBSS2540E.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Low power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current (DC)		-	-	-500	mA
I _{CM}	peak collector current		-	-	–1	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -500 \text{ mA};$ $I_B = -50 \text{ mA}$	<u>[1]</u> -	440	700	mΩ

[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



40 V, 500 mA PNP low V_{CEsat} (BISS) transistor

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline Symbol
1	base	
2	emitter	3
3	collector	
		sym013

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PBSS3540E	SC-75	plastic surface mounted package; 3 leads	SOT416	

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS3540E	1T

5. Limiting values

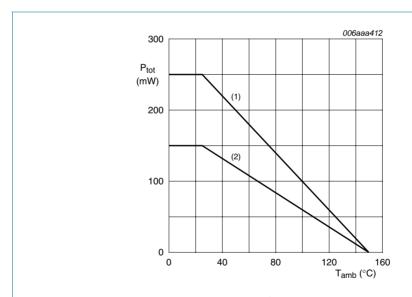
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Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current (DC)		-	-500	mA
I _{CM}	peak collector current		-	-1	А
I _{BM}	peak base current		-	-100	mA
P_{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	150	mW
			[2] _	250	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig 1. Power derating curves

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Thermal characteristics 6.

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Product data sheet

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	<u>[1]</u> -	-	833	K/W
	junction to ambient		[2] _	-	500	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

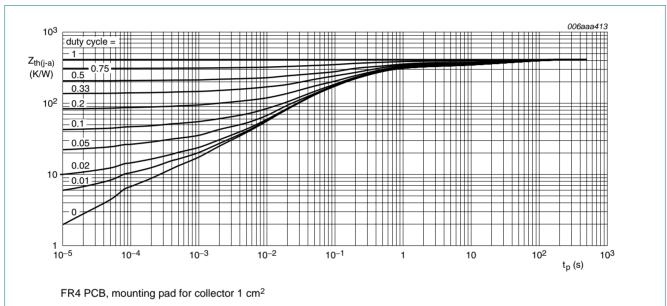


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



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40 V, 500 mA PNP low V_{CEsat} (BISS) transistor

Characteristics

Table 7. Characteristics

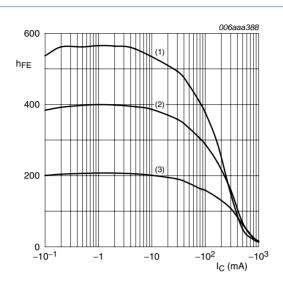
 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nΑ
	current	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -10 \text{ mA}$	200	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}$	<u>11</u> 150	-	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -500 \text{ mA}$	<u>[1]</u> 40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-50	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-130	mV
		$I_C = -200 \text{ mA}; I_B = -10 \text{ mA}$	-	-	-200	mV
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	<u>[1]</u> _	-	-350	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	<u>[1]</u> -	440	700	mΩ
V_{BEsat}	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1] -	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}$	-	-	-1.1	V
f⊤	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -100 \text{ mA;}$ f = 100 MHz	100	300	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	-	10	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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40 V, 500 mA PNP low V_{CEsat} (BISS) transistor



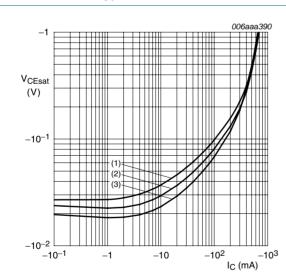
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. DC current gain as a function of collector current; typical values



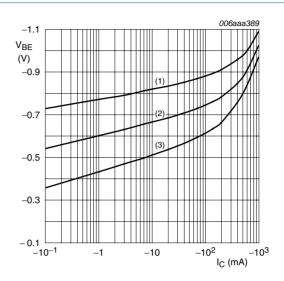
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



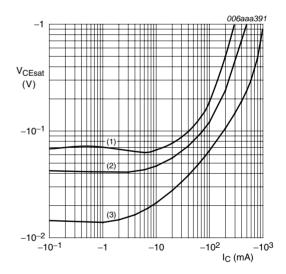
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Base-emitter voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

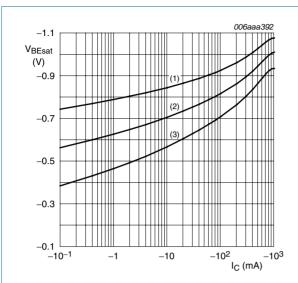
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

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40 V, 500 mA PNP low V_{CEsat} (BISS) transistor



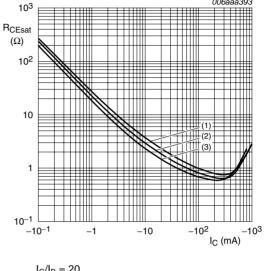
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter saturation voltage as a function of collector current; typical values



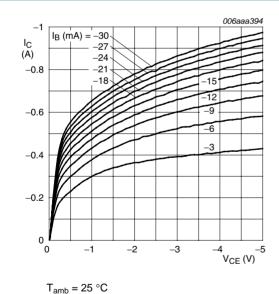
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

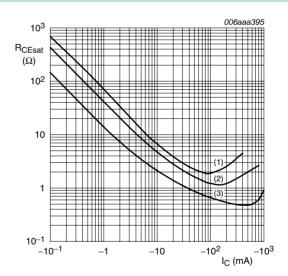
(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 8. Collector-emitter saturation resistance as a function of collector current; typical values



Collector current as a function of Fig 9. collector-emitter voltage; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

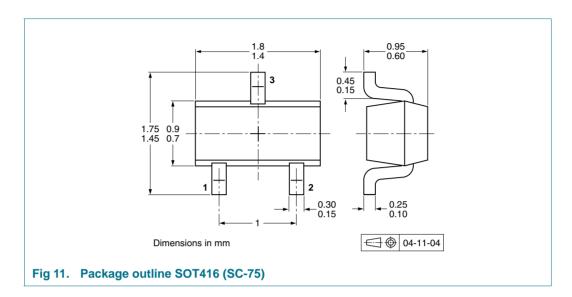
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

40 V, 500 mA PNP low V_{CEsat} (BISS) transistor

8. Package outline



9. Packing information

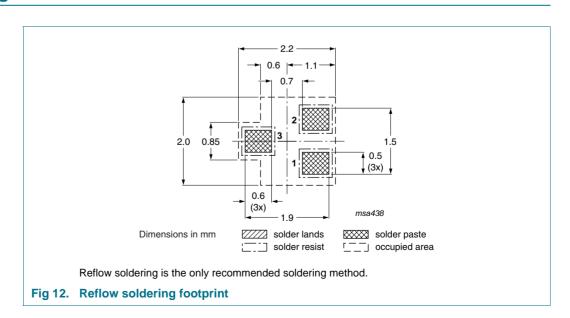
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing quantity		
			3000	10000
PBSS3540E	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 13.

10. Soldering



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11. Revision history

Table 9. **Revision history**

Product data sheet

Document ID Release date Data sheet status Change notice Supersedes PBSS3540E_2 20091211 Product data sheet - PBSS3540E_1 Modifications: • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 4 "Base-emitter voltage as a function of collector current; typical values": updated • Figure 12 "Reflow soldering footprint": updated - - PBSS3540E_1 20050503 Product data sheet - -		•			
Modifications: • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 4 "Base-emitter voltage as a function of collector current; typical values": updates • Figure 12 "Reflow soldering footprint": updated	Document ID	Release date	Data sheet status	Change notice	Supersedes
 including new legal definitions and disclaimers. No changes were made to the technical content. Figure 4 "Base-emitter voltage as a function of collector current; typical values": update Figure 12 "Reflow soldering footprint": updated 	PBSS3540E_2	20091211	Product data sheet	-	PBSS3540E_1
• Figure 12 "Reflow soldering footprint": updated	Modifications:	including nev			
		 Figure 4 "Ba 	se-emitter voltage as a fun	ction of collector curre	nt; typical values": updated
PBSS3540E_1 20050503 Product data sheet		Figure 12 "R	eflow soldering footprint": ι	ıpdated	
	PBSS3540E_1	20050503	Product data sheet	-	-

NXP Semiconductors PBSS3540E

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

PBSS3540E

40 V, 500 mA PNP low V_{CEsat} (BISS) transistor

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